

TRANSISTOR (PNP)

FEATURES

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary types: BCP54...BCP56 (NPN)

SOT-223 1. BASE 2. COLLECTOR 3. EMITTER

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	BCP51	BCP52	BCP53	Units
V _{CBO}	Collector-Base Voltage	-45	-60	-100	V
V _{CEO}	Collector-Emitter Voltage	-45	-60	-80	V
V _{EBO}	Emitter-Base Voltage -5		V		
Ic	Collector Current -Continuous -1		Α		
Pc	Collector Power Dissipation 1.5			W	
$R_{\theta JA}$	Thermal Resistance Junction to Ambient 94		°C/W		
T _{stg}	Storage Temperature Range -65to+150		$^{\circ}$		

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	BCP51			-45		
	BCP52	$V_{(BR)CBO}$	I _C =- 0.1mA,I _E =0	-60		V
	BCP53			-100		
Collector-emitter breakdown voltage BCP51				-45		
	BCP52	$V_{(BR)CEO}$	I _C = -10mA,I _B =0	-60		V
	BCP53			-80		
Base-emitter breakdown voltage		$V_{(BR)EBO}$	I _C = -10μA,I _E =0	-5		V
Collector cut-off current		I _{CBO}	V _{CB} = -30 V, I _E =0		-100	nA
		h _{FE(1)}	V _{CE} =-2V, I _C =-5mA	25		
DC current gain		h _{FE(2)}	V _{CE} = -2V, I _C =-150m A	63	250	
		h _{FE(3)}	V _{CE} = -2V, I _C =-500m A	25		
Collector-emitter saturation voltage		V _{CE(sat)}	I _C =-500mA,I _B =-50mA		-0.5	٧
Base-emitter voltage		V _{BE}	V _{CE} =-2V, I _C =-500m A		-1	V
Transition frequency		f⊤	V _{CE} =-10V,I _C =-50mA,f=100MHz	100		MHz

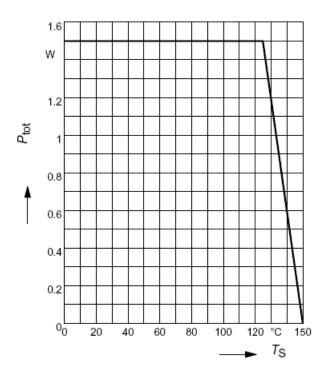
CLASSIFICATION OF h_{FE(2)}

Rank	BCP51-10, BCP52-10, BCP53-10	BCP51-16, BCP52-16, BCP53-16		
Range 63-160		100-250		

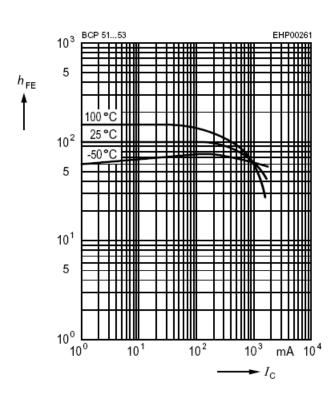


Typical Characteristics

Total power dissipation $P_{tot} = f(T_S)$

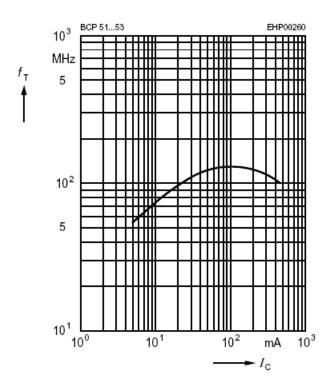


DC current gain $hFE = f(I_C)$



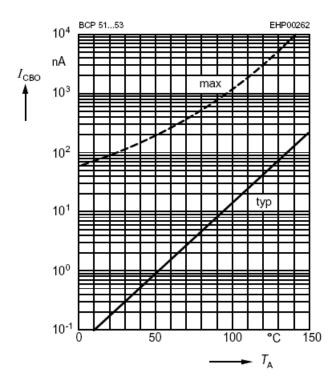
Transition frequency $f_T = f(I_C)$

$$V_{CE} = 10V$$



Collector cutoff current $I_{CBO} = f(T_A)$

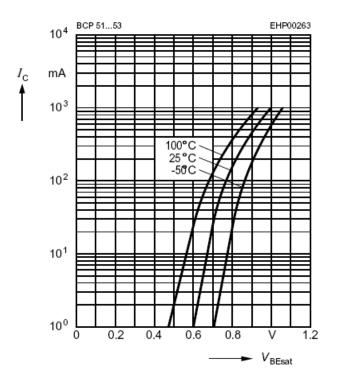
$$V_{CB} = 30V$$





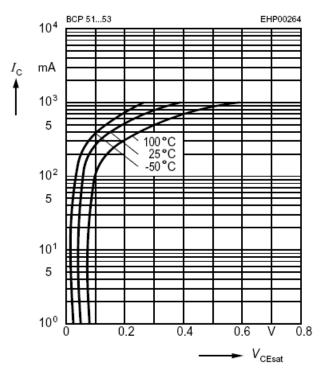
Base-emitter saturation voltage

$$I_{C} = f(V_{BEsat}), h_{FE} = 10$$



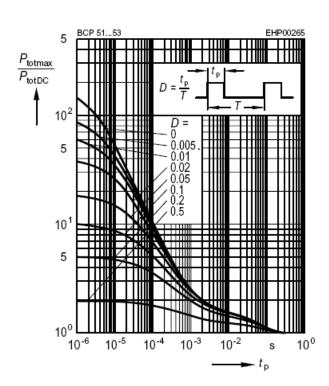
Collector-emitter saturation voltage

$$I_{C} = f(V_{CEsat}), h_{FE} = 10$$



Permissible pulse load

 $P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$



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